

9097250 TOSHIBA (DISCRETE/OPTO)

67C 09297

D. F-01-09

1S1553~1S1555

Silicon Epitaxial Planar Type

Diode

GENERAL PURPOSE APPLICATION FOR DETECTOR
AND RECTIFIER.

FEATURES:

- Low Forward Voltage : $V_F=1.0V$ (Typ.)
- Small Total Capacitance : $C_T=1.3pF$ (Typ.)

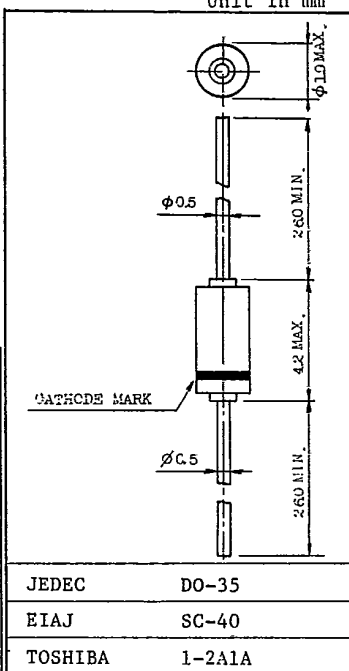
MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	1S1553	V_{RM}	70	V
	1S1554		55	
	1S1555		35	
Reverse Voltage	1S1553	V_R	60	V
	1S1554		50	
	1S1555		30	
Maximum (Peak) Forward Current		I_{FM}	300	mA
Average Forward Current		I_O	100	mA
Surge Current (1 sec)		I_{FSM}	1	A
Power Dissipation		P	300	mW
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-65~150	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage		V_F	$I_F=100mA$	-	1.0	1.4	V
Reverse Current	1S1553	I_R	$V_R=60V$	-	-	0.5	μA
	1S1554		$V_R=50V$				
	1S1555		$V_R=30V$				
Total Capacitance		C_T	$V_R=0$ $f=1MHz$	-	1.3	3.5	pF

Unit in mm



Weight : 0.14g

Marking

1S1553



1S1554



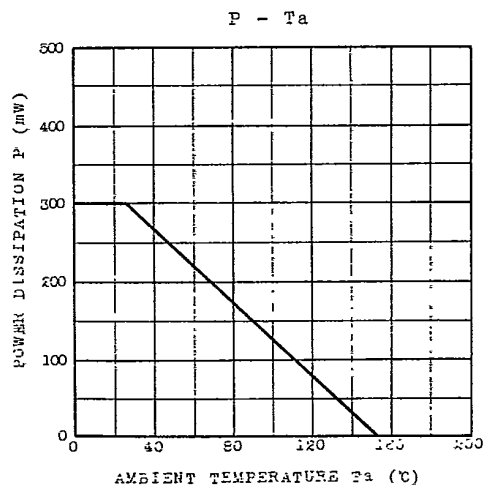
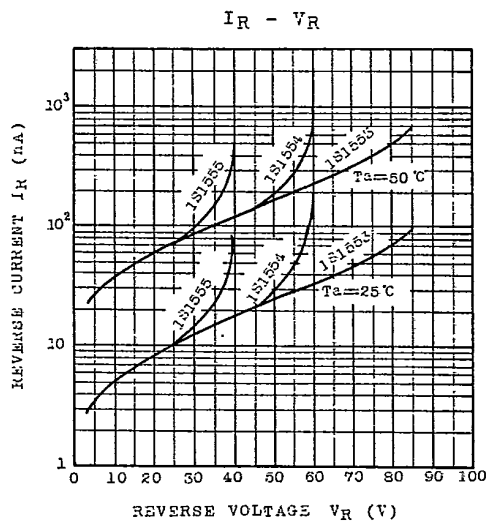
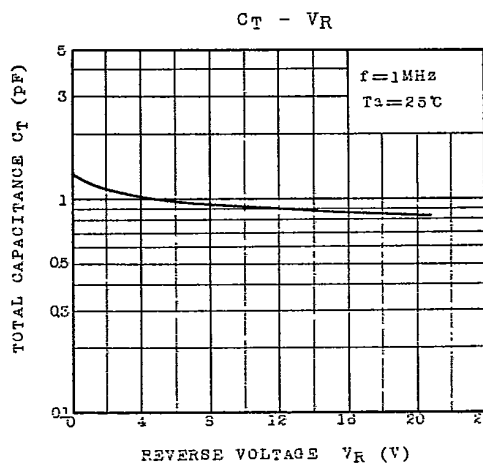
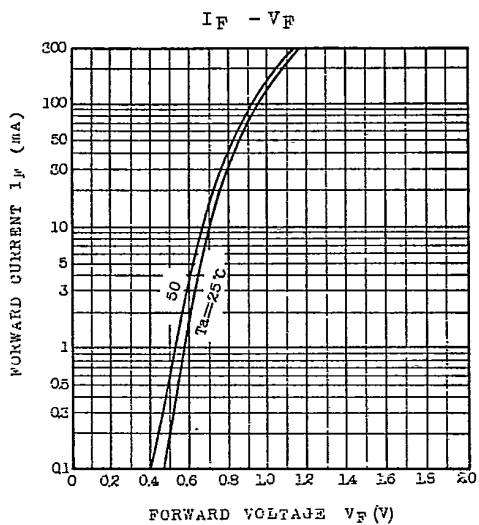
1S1555



9097250 TOSHIBA (DISCRETE/OPTO)

67C 09298 DT-01-09

1S1553~1S1555



TOSHIBA CORPORATION